

<b>INFORMATION DISCLOSURE STATEMENT</b>  	Atty. Docket No.: 150.01150103	Serial No.: 10/771,043
	Applicant(s): Gurtej S. Sandhu	Confirmation No.: 1538
	Application Filing Date: February 3, 2004	Group: 1743
	Information Disclosure Statement mailed: June 16, 2004	

## U.S. PATENT DOCUMENTS

Examiner Initial	Copy Enclosed	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
		5,653,807	08/05/97	Crumbaker			

## FOREIGN PATENT DOCUMENTS

Examiner Initial	Copy Enclosed	Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
Y6	X	1,576,658	08/01/69	France (w/abstract)			X	
Y6	X	2-293644	12/04/90	Japan (w/abstract)			X	
Y6	X	3-48748	03/01/91	Japan (w/abstract)			X	
Y6	X	2-69658	03/08/90	Japan (w/abstract)				X

## OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

Examiner Initial	Copy Enclosed	Document Description
Y6	X	Akinfieva, T.A., "Basis for the maximum allowable concentration of ruthenium dioxide in the air of work areas," <i>Gigiena Truda i Professional'nye Zabolevaniya</i> , 1981:46-47 (English Abstract Included)
	X	Crawford et al., "Use of the Hazop Analysis for Evaluation of CVD reactors," <i>Journal de Physique IV</i> , September 1991: C2-459- C2-466.
	X	Gale et al., "Interaction of Safety and the facility for Photovoltaic R & D," <i>American Institute of Physics Conference Proceedings</i> , 1988;66:145-151
	X	Koda et al., "Radioactivation determination of ruthenium," <i>Kyoto Daigaku Genshoro Jikkensho Gakujutsu Koenkai Koen Yoshishyu</i> , 1976;10:25-27. (English Translation)
	X	Lu et al., "Epitaxial growth of RuO <sub>2</sub> thin films by metal-organic chemical vapor deposition," <i>Thin Solid Films</i> , 1999;340:140-144.
	X	Orlow et al., "Detection of Ruthenium in Platinum Alloys," <i>Chemiker-Zeitung</i> , 1908;32:77. (English Translation)

EXAMINER	Date Considered
<i>Melvin Hale</i>	08/06/04
<small>*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>	

<b>INFORMATION DISCLOSURE STATEMENT</b>	Atty. Docket No.: 150.01150103	Serial No.: 10/771,043
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	Application Filing Date: February 3, 2004	Group: Unassigned
	Information Disclosure Statement mailed:	April 29, 2004

**U.S. PATENT DOCUMENTS**

Examiner Initial	Copy Enclosed	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
Y6		3,585,073	06/15/71	Veenstra et al.			
		3,890,703	06/75	Frazee et al.			
		4,433,320	02/21/84	Murata et al.			
		4,442,422	04/10/84	Murata et al.			
		4,677,416	06/30/87	Nishimoto et al.			
		4,911,892	03/27/90	Grace et al.			
		5,147,737	09/15/92	Post et al.			
		5,331,287	07/19/94	Yamagishi et al.			
		5,337,018	08/09/94	Yamagishi			
		5,756,879	05/26/98	Yamagishi et al.			
		5,857,250	01/12/99	Riley et al.			
		5,906,726	05/25/99	Schneider et al.			
		6,280,604	08/28/01	Allen et al.			
		6,436,246	08/20/02	Sandhu			
		6,479,297	11/12/02	Sandhu			
		6,689,321	02/10/04	Sandhu			
✓		US 2003/0138958	07/24/03	Blalock			

**FOREIGN PATENT DOCUMENTS**

Examiner Initial	Copy Enclosed	Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
		1,151,482	05/07/69	Great Britain				
		1,576,658	08/01/69	France (w/abstract)				X

<b>EXAMINER</b> <i>Helen Mel</i>	<b>Date Considered</b> <i>parent case 05/26/03</i>
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		2-293644	12/04/90	Japan (w/abstract)			X
		386,660	09/12/90	EP (w/abstract)			X
		3-48748	03/01/91	Japan (w/abstract)			X
		60-210752	10/85	Japan (w/abstract)			X
		2-69658	03/90	Japan			X

**OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)**

Examiner Initial	Copy Enclosed	Document Description
Y		Aizenshtein et al., "Method of measurement of the rate of deposition of pure metals from the gas phase," <i>Chem. Abstr.</i> , 1966; 64: abstract 1747e.
Y		Aizenshtein et al., "Method of Measuring Rate of Pure Metals Deposition from the gas phase," <i>Tsvetnye Metally The Soviet Journal of Non-Ferrous Metals</i> , 6(9): 72-74.
		Bardin et al., "Voltammetry of Ruthenate, Determination of Ruthenium from the Electrochemical Reduction of Ruthenium," <i>Journal of Analytical Chemistry of the USSR</i> , 1975;30: 642-645.
		Bates, J.R. et al., "The influence of the electrodeposition parameters on the morphology of organo-transition metal complexes for thin film gas sensor application", <i>Thin Solid Films</i> , 1997;299: 18-24.
		Brown et al., "New method for the characterization of domain morphology of polymer blends using ruthenium tetroxide staining and low voltage scanning electron microscopy (LVSEM)," <i>Polymer</i> , 1997; 38(15): 3937-3945,
		Kawahara et al., "(Ba,Sr)TiO <sub>3</sub> Films Prepared by Liquid Source Chemical Vapor Deposition on Ru Electrodes," <i>Jpn Journ Appl Phys</i> , 1996;35 (Part 1, No. 9B): 4880-4885.
		Kawahara et al., "(Ba, Sr)TiO <sub>3</sub> Films Prepared by Liquid Source Chemical Vapor Deposition on Ru Electrodes," <i>J. Appl. Phys.</i> , 1996;35: 4880-4885.
Y		Koda et al., "Radioactivation determination of ruthenium," <i>Chem Abstr</i> , 1979;90: abstract 114382q.

EXAMINER	<i>Helee</i>	Date Considered	<i>4/26/03</i>
<i>12/15/03-09/17/03</i>			
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Examiner Initial	Copy Enclosed	Document Description
Y6		Koda et al., "Radioactivation determination of ruthenium," <i>Kyoto Daigaku Genshiro Jikkensho Gakujutsu Koen Yoshishu</i> , 1976; 10: 25-27.
		Kolesov et al., "Role of surface moisture of samples in the determination of volume resistivity of polymers," <i>Chem Abstr</i> , 1989; 110: abstract 213848j.
		Li et al., "RuO <sub>4</sub> Staining and Lamellar Structure of $\alpha$ - and $\beta$ -PP," <i>J. Appl. Polym. Sci.</i> , 1999; 72: 1529-1538.
		Miyashita, Haruzo, "Particle Measurement in Vacuum Tools by In Situ Particle Monitor," <i>Aneruba Giho</i> , 1996; 2: 67-71.
		Morgunov et al., "Evaluation of the film structure imperfections from electric conductivity by the statistical analysis of data," <i>Chem Abstr</i> , 1982; 96: abstract 105113z.
		Ohlsson et al., "The Use of RuO <sub>4</sub> in Studies of Polymer Blends by Scanning Electron Microscopy," <i>J Appl. Polym. Sci.</i> , 1990; 41: 1189-1196.
		Orlow, N.A., "Über de Nachweis von Ruthenium in den Platinlegierungen," <i>Chemiker-Zeitung</i> , 1908; 32: 77.
		Orlow, "Detection of Ruthenium in Platinum Alloys," <i>Arch. Experiment. Pathol.</i> ; 43: 131. (with translation).
		Provo, J.L., "Film-thickness resistance monitor for dynamic control of vacuum-deposited films," <i>J. Vac. Sci. Technol.</i> , July/Aug 1975; 12(4): 946-952.
		Sano et al., "Lamellar morphologies of melt-crystallized polyethylene, isotactic polypropylene and ethylene-propylene copolymers by the RuO <sub>4</sub> staining technique," <i>Polymer</i> , October 1986; 27: 1497-1504.
		Setz et al., "Morphology and Mechanical Properties of Blends of Isotactic or Syndiotactic Polypropylene with SEBS Block Copolymers," <i>J. Appl. Poly. Sci.</i> , 1996; 59: 1117-1128.
		Shabasy et al., "Electrical properties of thin metal zinc films," <i>Journal of Material Science</i> , 1990; 25: 585-588.
Y		Schepis et al., "Influence of deposition rates and thickness on the electrical resistivity and thermoelectric power of thin iron films," <i>Thin Solid Films</i> , 1994; 251: 99-102.
EXAMINER	<i>Yelena Hale</i>	Date Considered <i>the present case</i>

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Y		Takayama et al., "Gas-Sensitive Ag Ion Conduction in Semiconducting ZnO Thin Films," <i>Solid State Ionics</i> , 1989; 35: 411-415.
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		Trent et al., "Ruthenium Tetraoxide Staining of Polymers for Electron Microscopy," <i>Macromolecules</i> , 1983; 16: 589-598.
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		Watari et al., "Present status of volatile ruthenium in analytical chemistry and health physics," <i>Chem Abstr.</i> , 1987;106:abstract 91861c.
		Watari et al., <i>Nihon Genshiryoku Gakkaishi</i> , 1986;28: 493-500.
		Watari et al., "Present Status of volatile ruthenium in analytical chemistry and health physics," <i>Nihon Genshiryoku Gakkaishi</i> , 1986;28(6): 15-22. (with translation).
✓		Yuan et al., "Low-Temperature Chemical Vapor Deposition of Ruthenium Dioxide from Ruthenium Tetroxide: A Simple Approach to High Purity RuO <sub>2</sub> Films," <i>Chem Mater</i> , 1993; 5: 908-910.

EXAMINER	<i>Yelen Hale</i>	Date Considered
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